John P R David

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/2924306/publications.pdf

Version: 2024-02-01

54	1,192	394421	395702
papers	citations	19	33
		h-index	g-index

54	54	54	909
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Temperature Dependence of the Impact Ionization Coefficients in AlAsSb Lattice Matched to InP. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-8.	2.9	11
2	Weibull-FrÃ©chet random path length model for avalanche gain and noise in photodiodes. Journal Physics D: Applied Physics, 2022, 55, 065105.	2.8	6
3	Comparison of the temperature dependence of impact ionization coefficients in AlAsSb, InAlAs, and InP. , 2022, , .		0
4	Theoretical Analysis of AlAsâ,€.â,…â,†Sbâ,€.â,„â,„ Single Photon Avalanche Diodes With High Breakdown Probability. IEEE Journal of Quantum Electronics, 2021, 57, 1-6.	1.9	1
5	Impact Ionization Coefficients in (Al_xGa_{1-x}) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 587 Td (Lattice-Matched to GaAs. IEEE Transactions on Electron Devices, 2021, 68, 4045-4050.	3.0	3
6	Valence band engineering of GaAsBi for low noise avalanche photodiodes. Nature Communications, 2021, 12, 4784.	12.8	20
7	Extremely low-noise avalanche photodiodes based on AlAs0.56Sb0.44. , 2020, , .		1
8	Extremely low excess noise and high sensitivity AlAs0.56Sb0.44 avalanche photodiodes. Nature Photonics, 2019, 13, 683-686.	31.4	62
9	Exact Analytical Formula for the Excess Noise Factor for Mixed Carrier Injection Avalanche Photodiodes. Journal of Lightwave Technology, 2019, 37, 3315-3323.	4.6	4
10	An excess noise measurement system for weak responsivity avalanche photodiodes. Measurement Science and Technology, 2018, 29, 065015.	2.6	1
11	Demonstration of large ionization coefficient ratio in AlAs0.56Sb0.44 lattice matched to InP. Scientific Reports, 2018, 8, 9107.	3.3	22
12	Assessing the Nature of the Distribution of Localised States in Bulk GaAsBi. Scientific Reports, 2018, 8, 6457.	3.3	28
13	Low-Noise Speed-Optimized Large Area CMOS Avalanche Photodetector for Visible Light Communication. Journal of Lightwave Technology, 2017, 35, 2315-2324.	4.6	13
14	White Light Constrained Multi-Primary Modulation for Visible Light Communication. , 2017, , .		7
15	Surface passivation of InAs avalanche photodiodes for low-noise infrared imaging. , 2016, , .		1
16	The staircase photodiode. Nature Photonics, 2016, 10, 364-366.	31.4	11
17	High-Gain InAs Planar Avalanche Photodiodes. Journal of Lightwave Technology, 2016, 34, 2639-2644.	4.6	8
18	InAs Diodes Fabricated Using Be Ion Implantation. IEEE Transactions on Electron Devices, 2015, 62, 2928-2932.	3.0	60

#	Article	IF	Citations
19	Relating the Experimental Ionization Coefficients in Semiconductors to the Nonlocal Ionization Coefficients. IEEE Transactions on Electron Devices, 2015, 62, 1946-1952.	3.0	23
20	InAs/GaSb Type-II Superlattice for Radiation Thermometry. IEEE Transactions on Instrumentation and Measurement, 2015, 64, 502-508.	4.7	6
21	Temperature dependence of avalanche multiplication and breakdown voltage in Al0.52In0.48P. Journal of Applied Physics, 2014, 115, .	2.5	9
22	Bismuth incorporation and the role of ordering in GaAsBi/GaAs structures. Nanoscale Research Letters, 2014, 9, 23.	5.7	56
23	Al<inline-formula><tex-math>$_{f 0.52}$</tex-math></inline-formula>In<inline-formula><tex-math>$_{f 0.48}$</tex-math></inline-formula>P SAM-APD as a Blue-Green Detector. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 142-146.	2.9	20
24	An Enhanced Color Shift Keying Modulation Scheme for High-Speed Wireless Visible Light Communications. Journal of Lightwave Technology, 2014, 32, 2582-2592.	4.6	172
25	Low breakdown voltage CMOS compatible p-n junction avalanche photodiode. , 2014, , .		5
26	High speed low noise InAs electron avalanche photodiodes for telecommunication and infrared sensing applications. , 2013, , .		3
27	Performance evaluation of IEEE 802.15.7 CSK physical layer. , 2013, , .		37
28	Absorption Characteristics of ${m GaAs}_{1-x}{m Bi}_{x}/{m GaAs}$ Diodes in the Near-Infrared. IEEE Photonics Technology Letters, 2012, 24, 2191-2194.	2.5	59
29	Short-Wave Infrared GaInAsSb Photodiodes Grown on GaAs Substrate by Interfacial Misfit Array Technique. IEEE Photonics Technology Letters, 2012, 24, 218-220.	2.5	27
30	InAs electron avalanche photodiodes with 580 GHz gain-bandwidth product. , 2012, , .		2
31	Low noise high responsivity InAs electron avalanche photodiodes for infrared sensing. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 310-313.	0.8	22
32	Effects of Dead Space on Avalanche Gain Distribution of X-Ray Avalanche Photodiodes. IEEE Transactions on Electron Devices, 2012, 59, 1063-1067.	3.0	11
33	Impact Ionization Coefficients in 4H-SiC by Ultralow Excess Noise Measurement. IEEE Transactions on Electron Devices, 2012, 59, 1030-1036.	3.0	12
34	Reverse leakage current mechanisms in quantum dot laser structures. , 2011, , .		0
35	Impact Ionization Coefficients in $hbox{Al}_{0.52} hbox{In}_{0.48}hbox{P}$. IEEE Electron Device Letters, 2011, 32, 1528-1530.	3.9	14
36	Sensitivity of High-Speed Lightwave System Receivers Using InAlAs Avalanche Photodiodes. IEEE Photonics Technology Letters, 2011, 23, 233-235.	2.5	20

#	Article	IF	Citations
37	High speed InAs electron avalanche photodiodes overcome the conventional gain-bandwidth product limit. Optics Express, 2011, 19, 23341.	3.4	95
38	Versatile Spectral Imaging With an Algorithm-Based Spectrometer Using Highly Tuneable Quantum Dot Infrared Photodetectors. IEEE Journal of Quantum Electronics, 2011, 47, 190-197.	1.9	16
39	Noise, Gain, and Responsivity in Low-Strain Quantum Dot Infrared Photodetectors With up to 80 Dot-in-a-Well Periods. IEEE Journal of Quantum Electronics, 2011, 47, 607-613.	1.9	5
40	Avalanche Multiplication and Excess Noise in InAs Electron Avalanche Photodiodes at 77 K. IEEE Journal of Quantum Electronics, 2011, 47, 858-864.	1.9	92
41	Temperature Dependence of Leakage Current in InAs Avalanche Photodiodes. IEEE Journal of Quantum Electronics, 2011, 47, 1123-1128.	1.9	43
42	Dark Current Mechanism in Bulk GaInNAs Lattice Matched to GaAs. IEEE Transactions on Electron Devices, 2011, 58, 103-106.	3.0	8
43	InAlAs Avalanche Photodiode With Type-II Superlattice Absorber for Detection Beyond 2 $muhbox{m}$. IEEE Transactions on Electron Devices, 2011, 58, 486-489.	3.0	24
44	GaInNAsSb/GaAs Photodiodes for Long-Wavelength Applications. IEEE Electron Device Letters, 2011, 32, 919-921.	3.9	2
45	Development of AlGaAs avalanche diodes for soft X-ray photon counting. , 2011, , .		0
46	GaAs p-i-n diodes for room temperature soft X-ray photon counting. , 2011, , .		0
47	Impact Ionization in InAs Electron Avalanche Photodiodes. IEEE Transactions on Electron Devices, 2010, 57, 2631-2638.	3.0	47
48	Electroluminescence Studies of Modulation p-Doped Quantum Dot Laser Structures. IEEE Journal of Quantum Electronics, 2010, 46, 1847-1853.	1.9	1
49	Sensitivity of high-speed receivers using InAlAs avalanche photodiodes. , 2010, , .		0
50	Optimization of InP APDs for High-Speed Lightwave Systems. Journal of Lightwave Technology, 2009, 27, 3294-3302.	4.6	19
51	Extremely Low Excess Noise in InAs Electron Avalanche Photodiodes. IEEE Photonics Technology Letters, 2009, 21, 866-868.	2.5	52
52	Dependence of the Electroluminescence on the Spacer Layer Growth Temperature of Multilayer Quantum-Dot Laser Structures. IEEE Journal of Quantum Electronics, 2009, 45, 79-85.	1.9	9
53	A Theoretical Comparison of the Breakdown Behavior of $hbox{In}_{0.52}hbox{Al}_{0.48}hbox{As}$ and InP Near-Infrared Single-Photon Avalanche Photodiodes. IEEE Journal of Quantum Electronics, 2009, 45, 566-571.	1.9	16
54	Effects of Ionization Velocity and Dead Space on Avalanche Photodiode Bit Error Rate. IEEE Transactions on Communications, 2007, 55, 2152-2158.	7.8	6